

Title (en)
INGAAS PHOTODIODE ARRAY

Title (de)
INGAAS-LICHTDIODENARRAY

Title (fr)
MATRICE DE PHOTODIODES INGAAS

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Application
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Abstract (en)
[origin: WO2013007753A1] The invention relates to an InGaAs photodiode array (101) and to the method for manufacturing same, wherein said array includes: a cathode including at least one indium-phosphide substrate layer (4) and an active gallium-indium arsenide layer (5); and a plurality of anodes (3) at least partially formed in the active gallium-indium arsenide layer by diffusing a P-type dopant, the interaction between an anode (3) and the cathode forming a photodiode. According to said method, an indium-phosphide passivation layer (6) is arranged on the active layer before the diffusion of the P-type dopant forming the anodes (3), and a first selective etching is performed so as to remove, over the entire thickness thereof, an area (10) of the passivation layer (6) surrounding each anode (3).

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US 2002011642 A1 20020131 - DRIES J CHRISTOPHER [US], et al

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